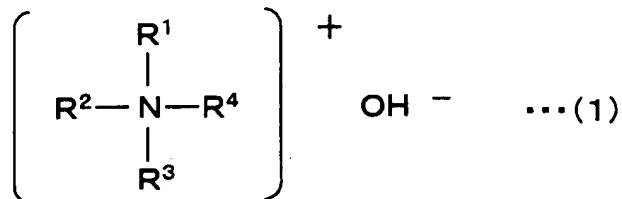


AMENDMENTS TO THE CLAIMS

1. (Original) A surface treatment method characterized by treating a surface with a supercritical fluid, wherein

an ammonium hydroxide expressed by the formula (1) below is added as a co-solvent agent to said supercritical fluid:



where each of R¹ to R⁴ in the formula (1) independently denotes an alkyl group, hydroxy-substituted alkyl group, aryl group or hydrogen.

2. (Currently Amended) ~~A~~The surface treatment method according to claim 1, wherein said surface has a structural body thereon.

3. (Currently Amended) The A-surface treatment method according to claim 2, wherein said structural body is a fine structural body with a hollow portion, a micro electromechanical systems, or an electrode pattern.

4. (Currently Amended) The A-surface treatment method according to claim 2, wherein said surface is that of a photomask utilized for lithography.

5. (Currently Amended) The A-surface treatment method according to claim 1, wherein said supercritical fluid is carbon dioxide.

6. (Currently Amended) The A-surface treatment method according to claim 1, wherein said supercritical fluid is further added with a surfactant material.

7. (Currently Amended) The A-surface treatment method according to claim 6, wherein said surfactant material is a polar solvent.

8. (Original) A surface treatment method characterized by treating a surface with a supercritical fluid, wherein

an alkanolamine expressed by the formula (2) below is added as a co-solvent agent to said supercritical fluid:



where each of R^1 to R^3 in formula (2) independently denotes an alkyl group, hydroxy-substituted alkyl group, aryl group or hydrogen.

9. (Currently Amended) The A-surface treatment method according to claim 8, wherein said surface has a structural body thereon.

10. (Currently Amended) The A-surface treatment method according to claim 9, wherein said structural body is a fine structural body with a hollow portion, a micro electromechanical systems, or an electrode pattern.

11. (Currently Amended) The A-surface treatment method according to claim 9, wherein said surface is that of a photomask utilized for lithography.

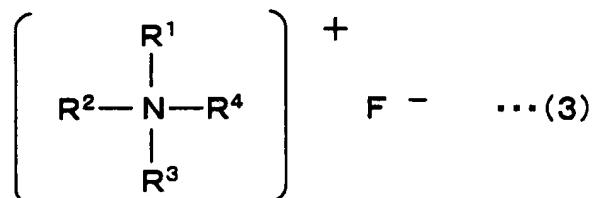
12. (Currently Amended) The A-surface treatment method according to claim 8, wherein said supercritical fluid is carbon dioxide.

13. (Currently Amended) The A-surface treatment method according to claim 8, wherein said supercritical fluid is further added with a surfactant material.

14. (Currently Amended) The A-surface treatment method according to claim 13, wherein said surfactant material is a polar solvent.

15. (Original) A surface treatment method characterized by treating a surface with a supercritical fluid, wherein

an amine fluoride expressed by the formula (3) below is added as a co-solvent agent to said supercritical fluid:



where each of R^1 to R^4 in the formula (3) independently denotes an alkyl group, hydroxy-substituted alkyl group, aryl group or hydrogen.

16. (Currently Amended) The A-surface treatment method according to claim 15, wherein said surface has a structural body thereon.

17. (Currently Amended) The A-surface treatment method according to claim 16, wherein said structural body is a fine structural body with a hollow portion, a micro electromechanical systems, or an electrode pattern.

18. (Currently Amended) The A-surface treatment method according to claim 16, wherein said surface is that of a photomask utilized for lithography.

19. (Currently Amended) The A-surface treatment method according to claim 15, wherein said supercritical fluid is carbon dioxide.

20. (Currently Amended) The A-surface treatment method according to claim 16, wherein said supercritical fluid is further added with a surfactant material.

21. (Currently Amended) The A-surface treatment method according to claim 20, wherein said surfactant material is a polar solvent.

22. (Original) A surface treatment method characterized by treating a surface with a supercritical fluid, wherein

hydrofluoric acid is added as a co-solvent agent to said supercritical fluid.

23. (Currently Amended) The A-surface treatment method according to claim 22, wherein said surface has a structural body thereon.

24. (Currently Amended) The A-surface treatment method according to claim 23, wherein said structural body is a fine structural body with a hollow portion, a micro electromechanical systems, or an electrode pattern.

25. (Currently Amended) The A-surface treatment method according to claim 23, wherein said surface is that of a photomask utilized for lithography.

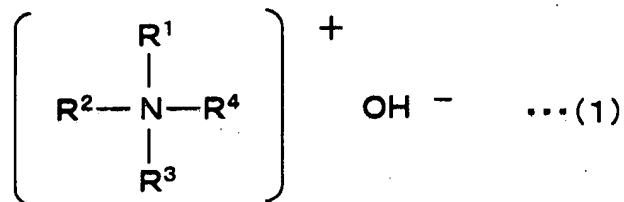
26. (Currently Amended) The A-surface treatment method according to claim 22, wherein said supercritical fluid is carbon dioxide.

27. (Currently Amended) The A-surface treatment method according to claim 22, wherein said supercritical fluid is further added with a surfactant material.

28. (Currently Amended) The A-surface treatment method according to claim 27, wherein said surfactant material is a polar solvent.

29. (Original) A semiconductor device obtainable by a surface treatment method characterized by treating a surface with a supercritical fluid, wherein

an ammonium hydroxide expressed by the formula (1) below is added as a co-solvent agent to said supercritical fluid:



where each of R^1 to R^4 in the formula (1) independently denotes an alkyl group, hydroxy-substituted alkyl group, aryl group or hydrogen.

30. (Original) A semiconductor device obtainable by a surface treatment method characterized by treating a surface with a supercritical fluid, wherein

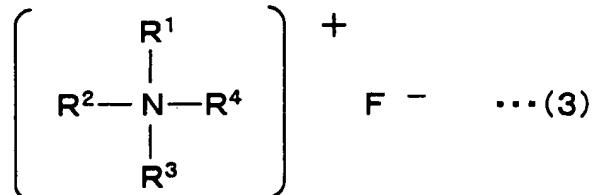
an alkanolamine expressed by the formula (2) below is added as a co-solvent agent to said supercritical fluid:



where each of R^1 to R^3 in formula (2) independently denotes an alkyl group, hydroxy-substituted alkyl group, aryl group or hydrogen.

31. (Original) A semiconductor device obtainable by a surface treatment method characterized by treating a surface with a supercritical fluid, wherein

an amine fluoride expressed by the formula (3) below is added as a co-solvent agent to said supercritical fluid:

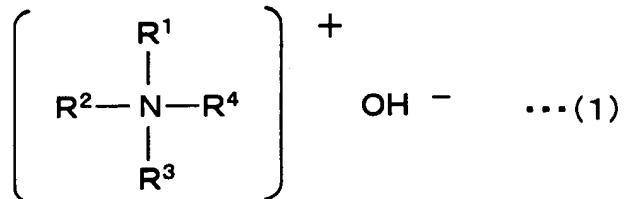


where each of R^1 to R^4 in the formula (3) independently denotes an alkyl group, hydroxy-substituted alkyl group, aryl group or hydrogen.

32. (Original) A semiconductor device obtainable by a surface treatment method characterized by treating a surface with a supercritical fluid, wherein hydrofluoric acid is added as a co-solvent agent to said supercritical fluid.

33. (Original) A method of fabricating a semiconductor device, said method comprising; adding an ammonium hydroxide expressed by the formula (1) below as a co-solvent agent to a supercritical fluid, and

treating a surface of said semiconductor device with said supercritical fluid:



where each of R¹ to R⁴ in the formula (1) independently denotes an alkyl group, hydroxy-substituted alkyl group, aryl group or hydrogen.

34. (Original) A method of fabricating a semiconductor device, said method comprising; adding an alkanolamine expressed by the formula (2) below as a co-solvent agent to a supercritical fluid, and

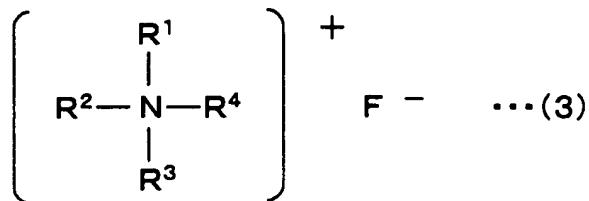
treating a surface of said semiconductor device with said supercritical fluid:



where each of R¹ to R³ in formula (2) independently denotes an alkyl group, hydroxy-substituted alkyl group, aryl group or hydrogen.

35. (Original) A method of fabricating a semiconductor device, said method comprising adding an amine fluoride expressed by the formula (3) below as a co-solvent agent to a supercritical fluid, and

treating a surface of said semiconductor device with said supercritical fluid:



where each of R^1 to R^4 in the formula (3) independently denotes an alkyl group, hydroxy-substituted alkyl group, aryl group or hydrogen.

36. (Original) A method of fabricating a semiconductor device, said method comprising; adding hydrofluoric acid as a co-solvent agent to a supercritical fluid, and treating a surface of said semiconductor device with said supercritical fluid.

37. (Original) A treatment apparatus comprising;
 a treatment chamber for housing therein a substrate to be treated,
 an opening through which said substrate is loaded and unloaded,
 a lid provided with said opening for tightly closing the inner space of said treatment chamber,
 a sealing member held between said treatment chamber and said lid, so that the inner space of said treatment chamber can be kept air-tight,
 a fluid supply port provided with said treatment chamber, and
 a fluid supply source connected to said fluid supply port, supplying a substance capable of having a form of supercritical fluid.

38. (Currently Amended) The A-treatment apparatus according to claim 37, wherein;
said fluid supply source is capable of supplying said substance capable of having a form of supercritical fluid in a gas form.

39. (Currently Amended) The A-treatment apparatus according to claim 37, further comprising; a valve for discharging said substance capable of having a form of supercritical fluid in said treatment chamber.

~~a valve for discharging said substance capable of having a form of supercritical fluid in said treatment chamber.~~

40. (Currently Amended) The A-treatment apparatus according to claim 39, further comprising; a discharge fluid separation device connected to said valve.

~~a discharge fluid separation device connected to said valve.~~

41. (Currently Amended) The A-treatment apparatus according to claim 40, further comprising; a heating means provided with said treating chamber for heating said supercritical substance.

~~a heating means provided with said treating chamber for heating said supercritical substance.~~